

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	("6753260").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/10 10:57
L2	2	("6873057").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/10 13:28
L3	0	("s9and(OSGnear2"dielectriclayer")").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/10 13:29
L7	100	damascene and (dielectric or ILD) near2 ("organo-silicate glass" or osg)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/10 13:32
S1	2209	(257/774).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/06 15:56
S3	996	(438/672).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/09 09:21
S4	1451	(438/687).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/09 09:40
S5	889	damascene and "etch stop".ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 09:41

S6	197	damascene and "etch stop".ti.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 09:47
S7	34	damascene and ("etch stop" with (composit or multi-layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 09:50
S8	121	damascene and ("etch stop" with (composite or multi-layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 16:28
S10	3	("6177364" "6440838" "6498399").PN. OR ("6734116"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/09 10:32
S11	273	taiwan.as. and damascene and "etch stop"	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/09 10:32
S12	358	taiwan.as. and damascene and "etch stop"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:47
S13	2	("6734116").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/09 10:40
S14	61	damascene and ("etch stop" with (composite or multi-layer)) and "low-k"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 12:26
S15	2	("6753260").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/09 12:26

S16	130	S12 and "low-k"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:17
S17	182	("spin on glass" or SOG) and "tensile stress"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:17
S18	32	("spin on glass" or SOG) with "tensile stress"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:23
S19	1	("spin on polymer" or SOp) with "tensile stress"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:24
S20	1	("spin-on-polymer" or SOp) with "tensile stress"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:24
S21	1	((spin adj on adj polymer) or SOp) with "tensile stress"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:25
S22	32	((spin adj on adj glass) or SOG) with "tensile stress"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:33
S23	8	"film hardness" and FSG	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:36

S24	0	hardness with "spin of glass"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:37
S25	0	hardness with "spin on glass"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:37
S26	0	hardness same "spin on glass"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:37
S27	17	hardness with SOG	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:49
S28	8	GPa with SOG	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:51
S29	0	hardness and spin adj on adj glass	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:07
S30	17	(etch\$3 near2 selectivity) with (SiCN)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:14
S31	2	(etch\$3 near2 selectivity) with (SiCN and SiCO)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:19

S32	7	(etch\$3 near2 selectivity) with (SiCN and (SiCO or SiOC))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:53
S33	0	("10365924").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/09 15:32
S34	0	"10365924".ap.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:33
S35	17	(etch\$3 adj selectivity) with (SiCN)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:39
S36	0	("200400161535").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/09 15:41
S37	2	("0161535").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/09 15:40
S38	5	"414467".ap.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:41
S39	114	S12 and selectivity	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:48

S40	8	(selectivity) with (SiCN and (SiCO or SiOC))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:53
S41	50	damascene and ("etch stop" with (composite or multi-layer)) and "silicon carbide" and ("silicon dioxide" or "silicon oxide")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/10 09:15